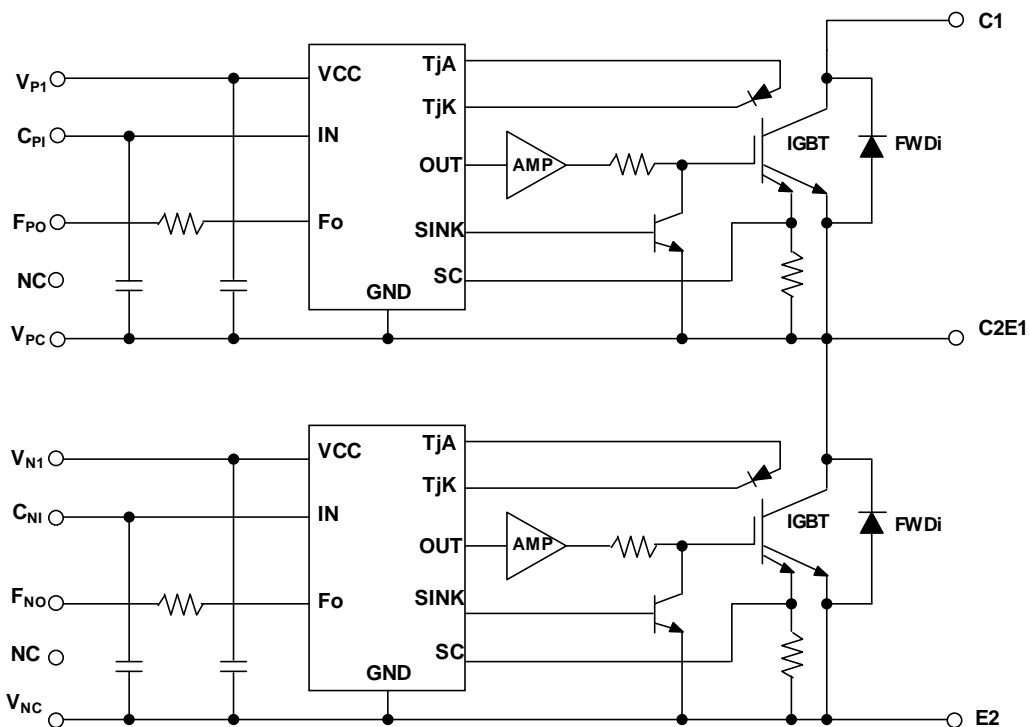


INTERNAL FUNCTIONS BLOCK DIAGRAM



MAXIMUM RATINGS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-Emitter Voltage	V _D =15V, V _{CIN} =15V	600	V
I _C	Collector Current	T _C =25°C	800	A
I _{CRM}		Pulse	1600	
P _{tot}	Total Power Dissipation	T _C =25°C	2500	W
I _E	Emitter Current	T _C =25°C	800	A
I _{ERM}	(Free wheeling Diode Forward current)	Pulse	1600	
T _j	Junction Temperature		-20 ~ +150	°C

*: T_c measurement point is just under the chip.

CONTROL PART

Symbol	Parameter	Conditions	Ratings	Unit
V _D	Supply Voltage	Applied between : V _{P1} -V _{PC} , V _{N1} -V _{NC}	20	V
V _{CIN}	Input Voltage	Applied between : C _{PI} -V _{PC} , C _{NI} -V _{NC}	20	V
V _{FO}	Fault Output Supply Voltage	Applied between : F _{PO} -V _{PC} , F _{NO} -V _{NC}	20	V
I _{FO}	Fault Output Current	Sink current at F _{PO} , F _{NO} terminals	20	mA

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TOTAL SYSTEM

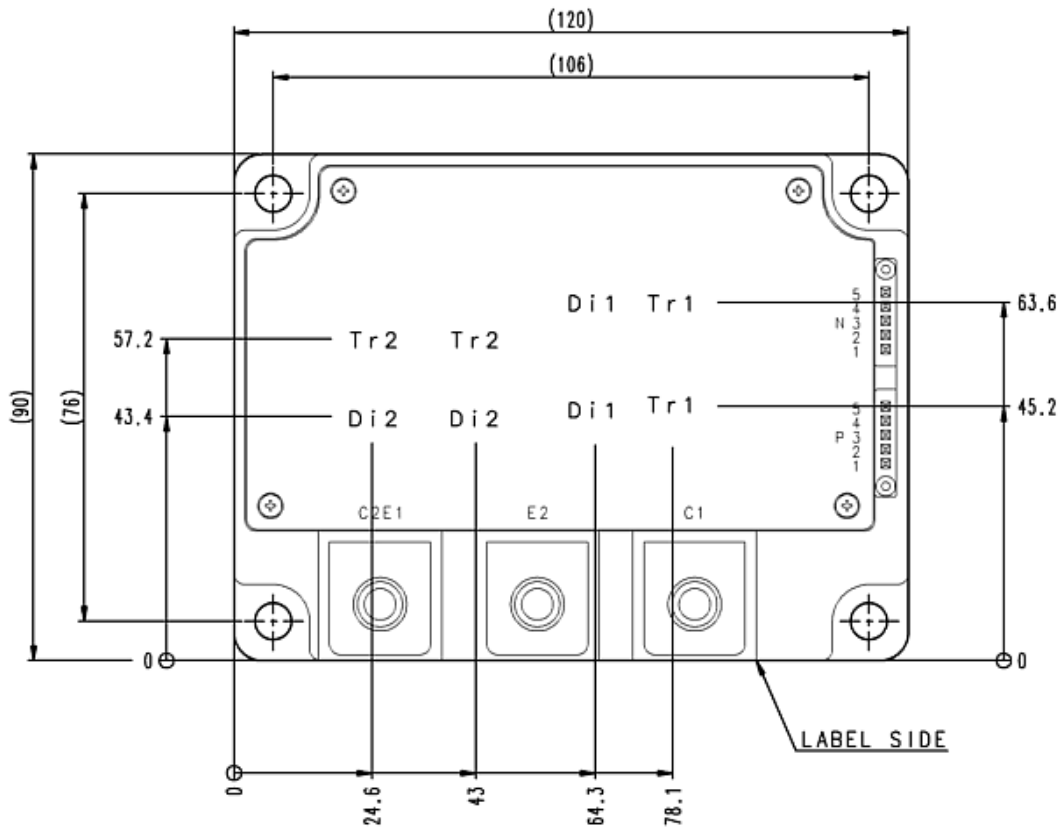
Symbol	Parameter	Conditions	Ratings	Unit
$V_{CC(prot)}$	Supply Voltage Protected by SC	$V_D = 13.5V \sim 16.5V$ Inverter Part, $T_j = +125^\circ C$ Start	400	V
$V_{CC(surge)}$	Supply Voltage (Surge)	Applied between : C1-E2, Surge value	500	V
T_C	Module case operating temperature		-20 ~ +100	$^\circ C$
T_{stg}	Storage Temperature		-40 ~ +125	$^\circ C$
V_{isol}	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base plate, AC 1min, RMS	2500	V

*: T_C measurement point is just under the chip.

THERMAL RESISTANCE

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal Resistance	Junction to case, IGBT (per 1 element) (Note.1)	-	-	0.05	K/W
$R_{th(j-c)D}$		Junction to case, FWDi (per 1 element) (Note.1)	-	-	0.09	
$R_{th(c-s)}$	Contact Thermal Resistance	Case to heat sink, (per 1 module) Thermal grease applied (Note.1)	-	0.014	-	

Note1: If you use this value, $R_{th(s-a)}$ should be measured just under the chips.



ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
V _{CEsat}	Collector-Emitter Saturation Voltage	V _D =15V, I _C =800A	T _j =25°C	-	1.85	2.35	V
		V _{CIN} =0V, Pulsed (Fig. 1)	T _j =125°C	-	1.85	2.35	
V _{EC}	Emitter-Collector Voltage	I _E =800A, V _D =15V, V _{CIN} =15V (Fig. 2)		-	1.7	2.8	V
t _{on}	Switching Time	V _D =15V, V _{CIN} =0V↔15V V _{CC} =300V, I _C =800A T _j =125°C Inductive Load (Fig. 3,4)		0.3	0.8	2.0	μs
t _{rr}				-	0.25	0.8	
t _{c(on)}				-	0.4	1.0	
t _{off}				-	1.4	2.3	
t _{c(off)}				-	0.3	1.0	
I _{CES}	Collector-Emitter Cut-off Current	V _{CE} =V _{CES} , V _D =15V, V _{CIN} =15V (Fig. 5)	T _j =25°C	-	-	1	mA
			T _j =125°C	-	-	10	

CONTROL PART

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _D	Circuit Current	V _D =15V, V _{CIN} =15V	V _{P1} -V _{PC}	-	2	4	mA
			V _{N1} -V _{NC}	-	2	4	
V _{th(ON)}	Input ON Threshold Voltage	Applied between : C _{P1} -V _{PC} , C _{N1} -V _{NC}		1.2	1.5	1.8	V
V _{th(OFF)}	Input OFF Threshold Voltage			1.7	2.0	2.3	
SC	Short Circuit Trip Level	-20≤T _j ≤125°C, V _D =15V (Fig. 3, 6)		1200	-	-	A
t _{off(SC)}	Short Circuit Current Delay Time	V _D =15V (Fig. 3, 6)		-	0.2	-	μs
OT	Over Temperature Protection	Detect Temperature of IGBT chip	Trip level	135	-	-	°C
OT _(hys)			Hysteresis	-	20	-	
UV _i	Supply Circuit Under-Voltage Protection	-20≤T _j ≤125°C	Trip level	11.5	12.0	12.5	V
UV _r			Reset level	-	12.5	-	
I _{FO(H)}	Fault Output Current	V _D =15V, V _{FO} =15V (Note.2)		-	-	0.01	mA
I _{FO(L)}				-	10	15	
t _{FO}	Fault Output Pulse Width	V _D =15V (Note.2)		1.0	1.8	-	ms

Note.2: Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

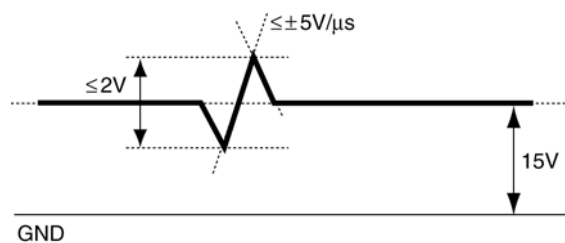
MECHANICAL RATINGS AND CHARACTERISTICS

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_s	Mounting Torque	Mounting part screw : M6	3.92	4.9	5.88	N·m
M_t		Main terminal part screw : M8	8.83	9.81	10.8	
m	Weight	-	-	720	-	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Conditions	Recommended value	Unit
V_{CC}	Supply Voltage	Applied across C1-E2 terminals	≤ 400	V
V_D	Control Supply Voltage	Applied between : $V_{P1}-V_{PC}$, $V_{N1}-V_{NC}$ (Note.3)	15.0 ± 1.5	V
$V_{CIN(ON)}$	Input ON Voltage	Applied between : $C_{P1}-V_{PC}$, $C_{N1}-V_{NC}$	≤ 0.8	V
$V_{CIN(OFF)}$	Input OFF Voltage		≥ 4.0	
f_{PWM}	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t_{dead}	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 3.0	μs

Note3: With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak



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PRECAUTIONS FOR TESTING

1. Before applying any control supply voltage (V_D), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
 After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
 (These test should not be done by using a curve tracer or its equivalent.)

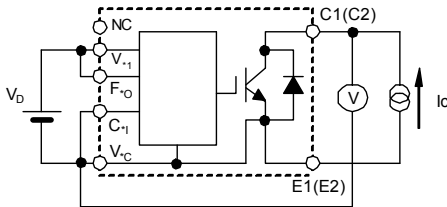


Fig. 1 V_{CESat} Test

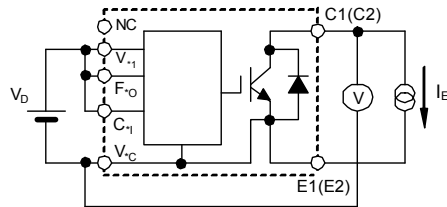


Fig. 2 V_{EC} Test

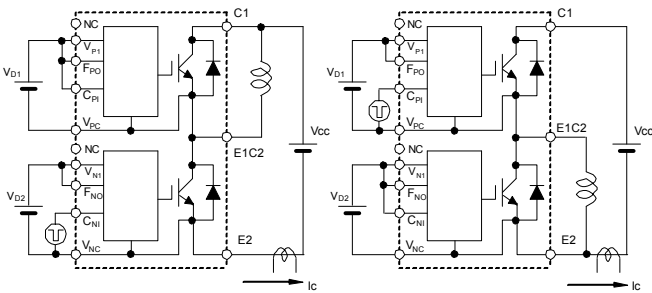


Fig. 3 Switching time and SC test circuit

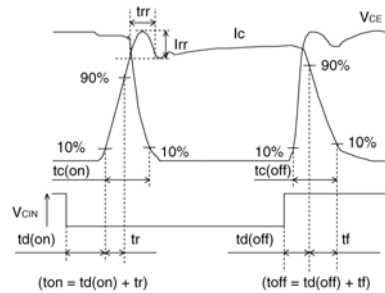


Fig. 4 Switching time test waveform

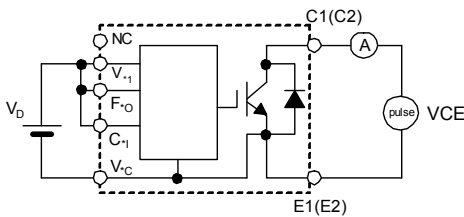


Fig. 5 I_{CES} Test

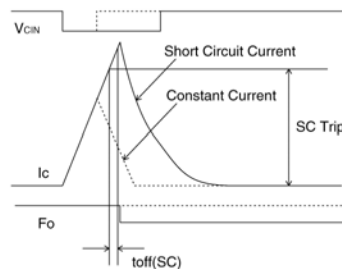
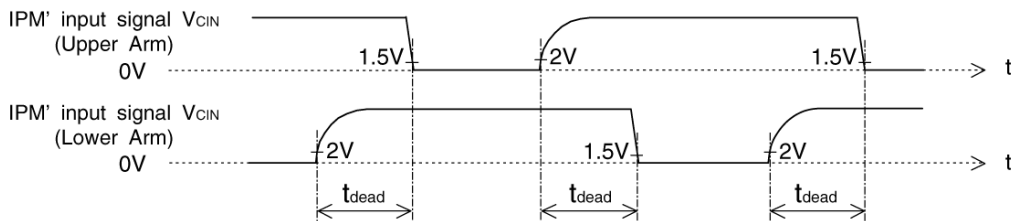


Fig. 6 SC test waveform



1.5V: Input on threshold voltage $V_{th(on)}$ typical value, 2V: Input off threshold voltage $V_{th(off)}$ typical value

Fig. 7 Dead time measurement point example

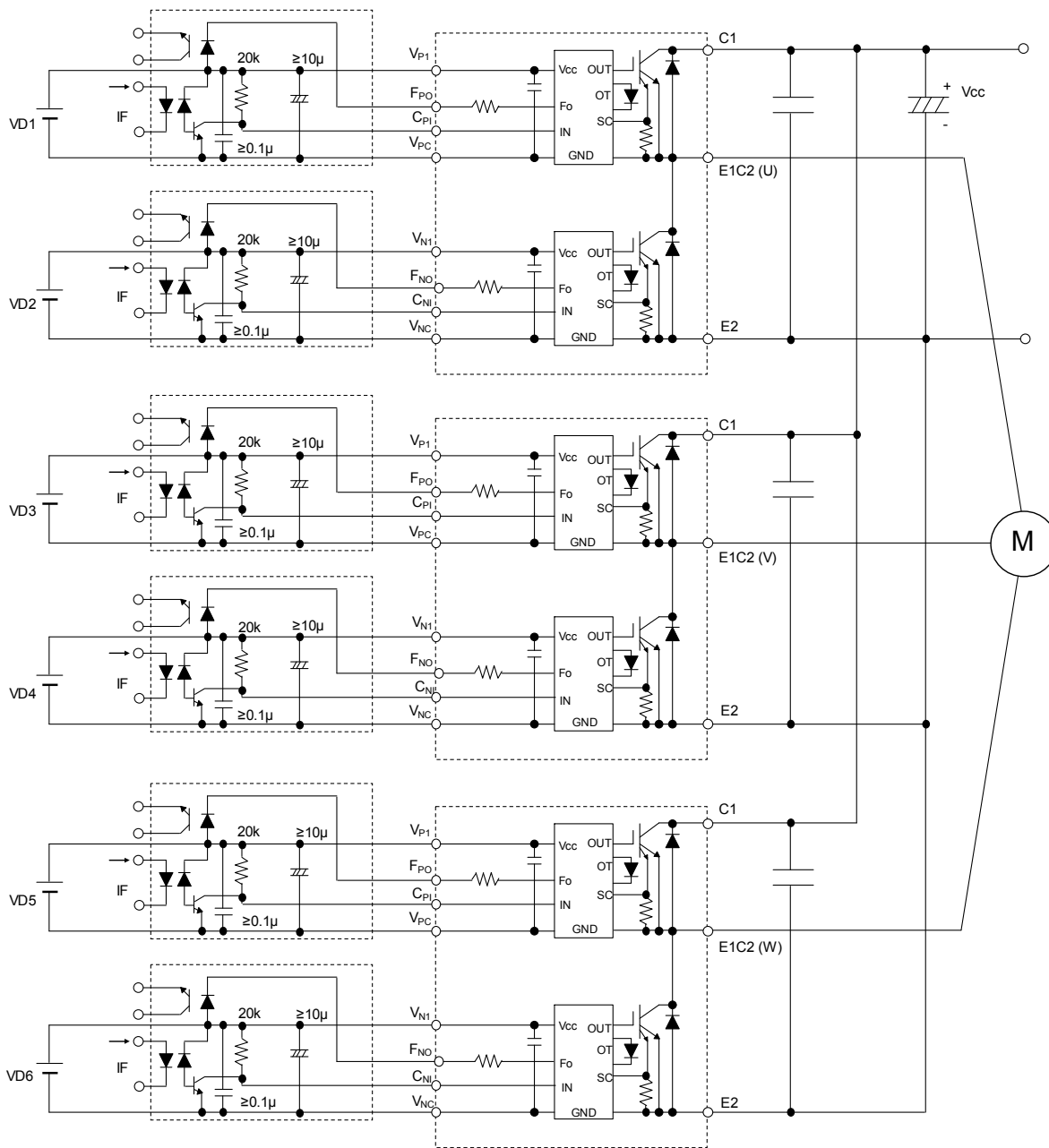


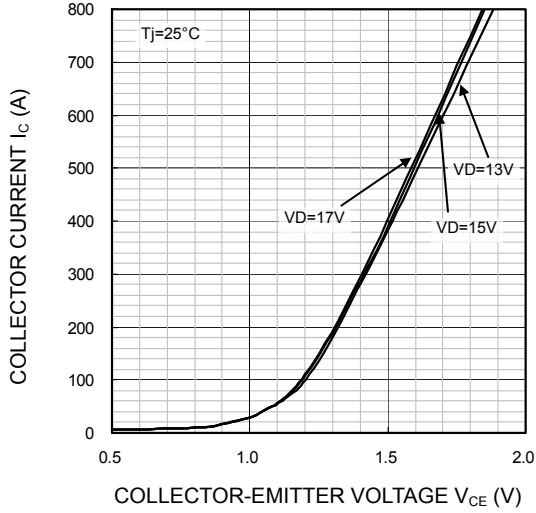
Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION ;

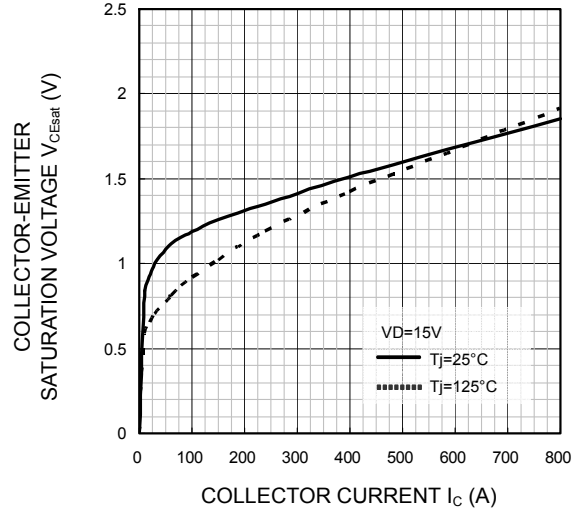
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: $t_{PLH}, t_{PHL} \leq 0.8\mu s$, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 6 isolated control power supplies (V_D). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between C1 and E2 terminal.

PERFORMANCE CURVES

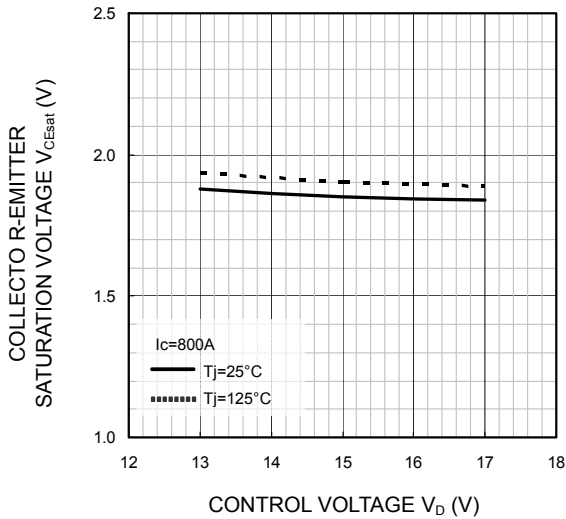
OUTPUT CHARACTERISTICS (TYPICAL)



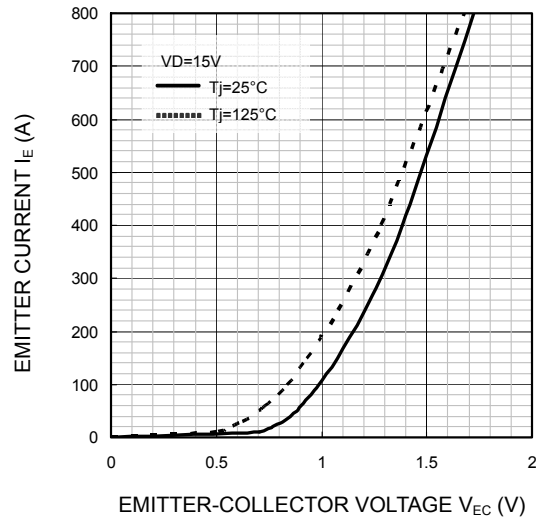
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. I_c) CHARACTERISTICS (TYPICAL)



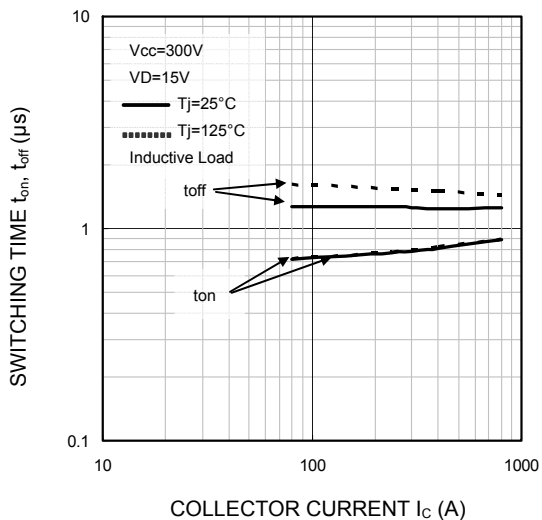
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. V_D) CHARACTERISTICS (TYPICAL)



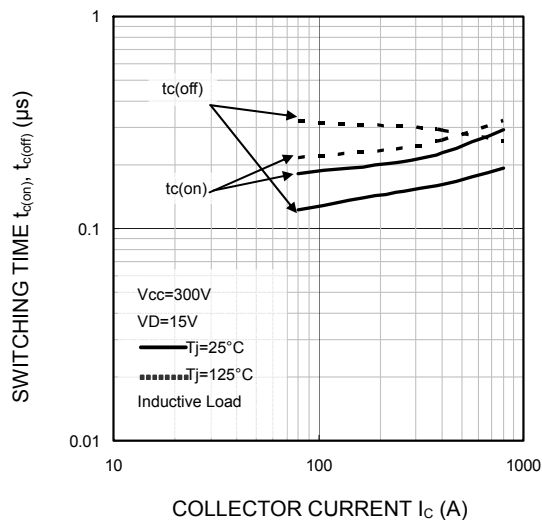
FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



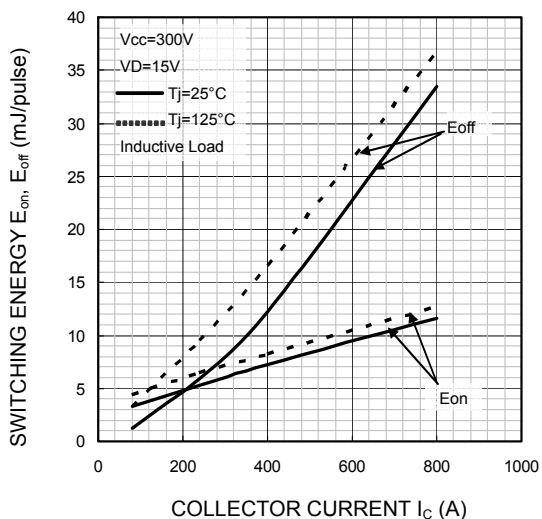
SWITCHING TIME (t_{on} , t_{off}) CHARACTERISTICS (TYPICAL)



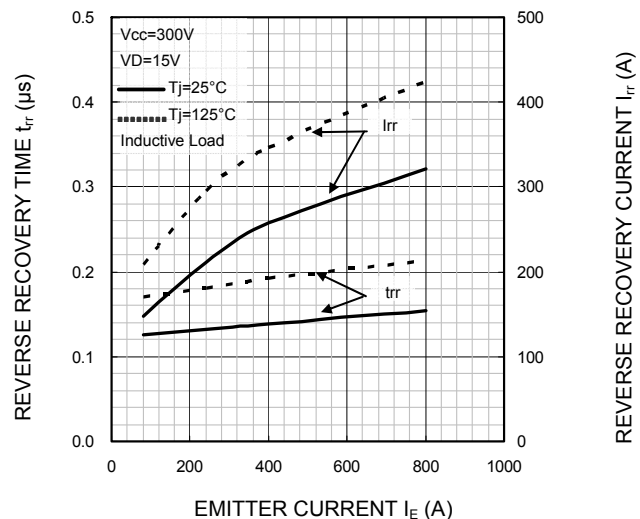
SWITCHING TIME ($t_{c(on)}$, $t_{c(off)}$) CHARACTERISTICS (TYPICAL)



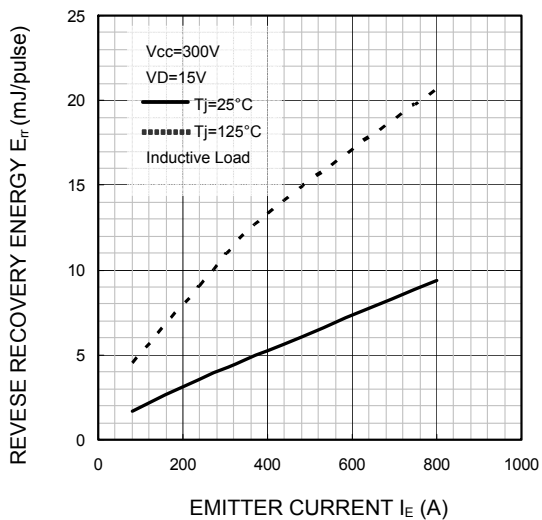
SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



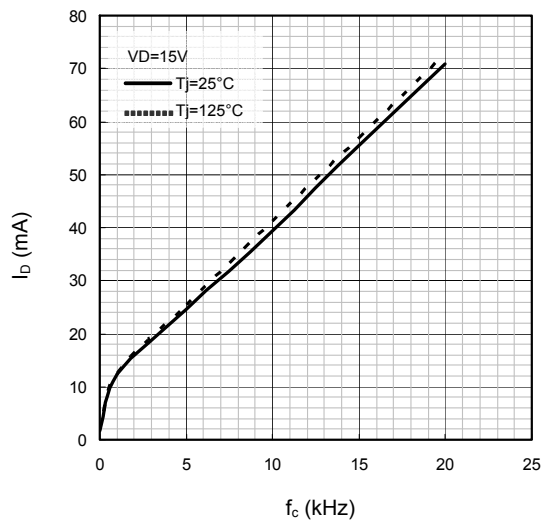
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



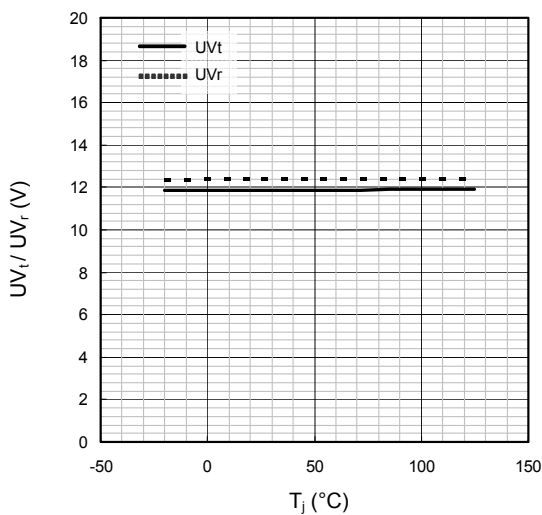
**FREE WHEELING DIODE
REVERSE RECOVERY ENERGY CHARACTERISTICS
(TYPICAL)**



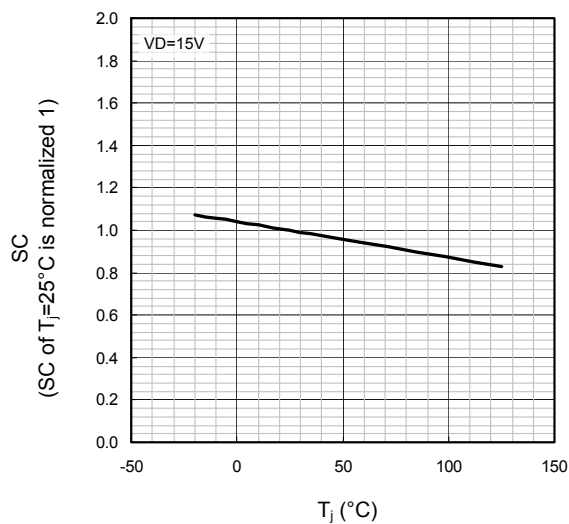
**I_b VS. f_c CHARACTERISTICS
(TYPICAL)**

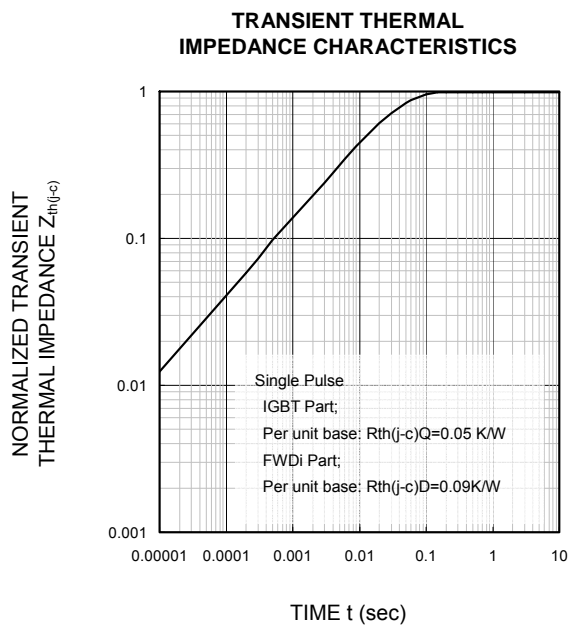


**UV TRIP LEVEL VS. T_j CHARACTERISTICS
(TYPICAL)**



**SC TRIP LEVEL VS. T_j CHARACTERISTICS
(TYPICAL)**





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Main Revision for this Edition

No.	Date	Revision	
		Pages	Points
1	November 2011	8	Output characteristics , "VD=13V" and "VD=17V" were reversed.

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